



CSTS150N10G N-Ch 100V Fast Switching MOSFETs

CSTS150N10G Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low RDS(ON)

CSTS150N10G Product Summary

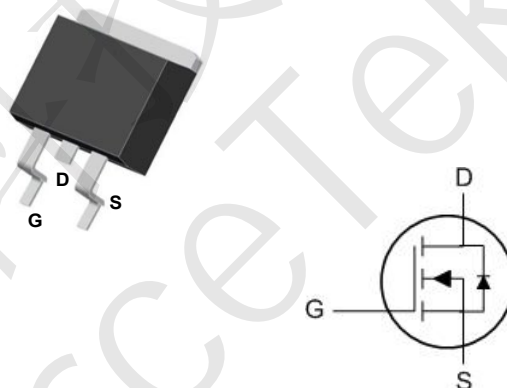


BVDSS	RDSON	ID
100V	3.1 mΩ	150A

CSTS150N10G Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

CSTS150N10G TO* Pin Configuration



CSTS150N10G Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DS}	100	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I _D	T _C = 25°C	150
		T _C = 100°C	96
Pulsed Drain Current ⁽²⁾	I _{DM}	619	A
Avalanche Energy ⁽³⁾	E _{AS}	726	mJ
Power Dissipation ⁽⁴⁾	P _D	T _C = 25°C	312
		T _C = 100°C	125
Junction & Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C



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CSTS150N10G Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0	3.0	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		3.1	3.6	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		50		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.66	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			150	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}			4797		pF
Output Capacitance	C_{oss}	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		900		pF
Reverse Transfer Capacitance	C_{rss}			19.1		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		1.9		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g			84		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g	$V_{GS} = 0$ to 10V		57		nC
Gate Source Charge	Q_{gs}	$V_{DS} = 50\text{V}, I_D = 20\text{A}$		24		nC
Gate Drain Charge	Q_{gd}			27		nC
Turn-On DelayTime	$t_{D(on)}$			21		ns
Turn-On Rise Time	t_r	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$		35		ns
Turn-Off DelayTime	$t_{D(off)}$	$R_L = 2.5\Omega, R_{GEN} = 3\Omega$		49		ns
Turn-Off Fall Time	t_f			30		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		71		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		127		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	55	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.40	0.60	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. E_{AS} of 726 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 22\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$; 100% test at $L = 0.3\text{mH}$, $I_{AS} = 45\text{A}$, $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.



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CSTS150N10G Typical Electrical & Thermal Characteristics

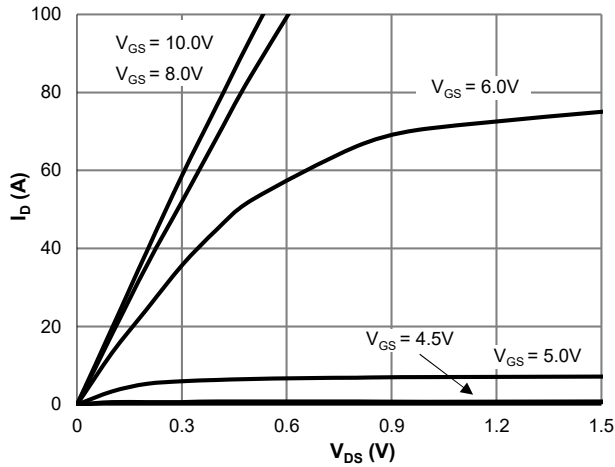


Figure 1: Saturation Characteristics

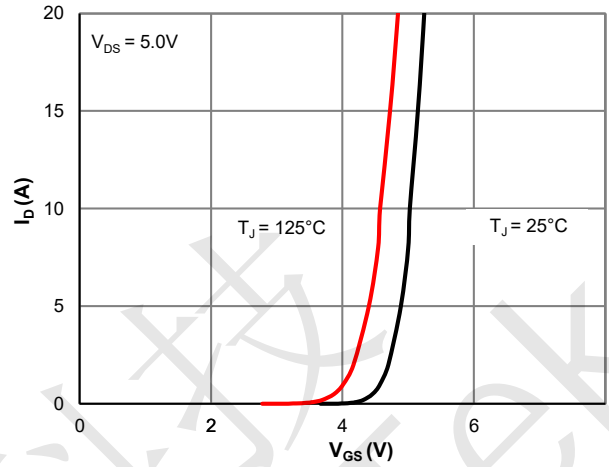


Figure 2: Transfer Characteristics

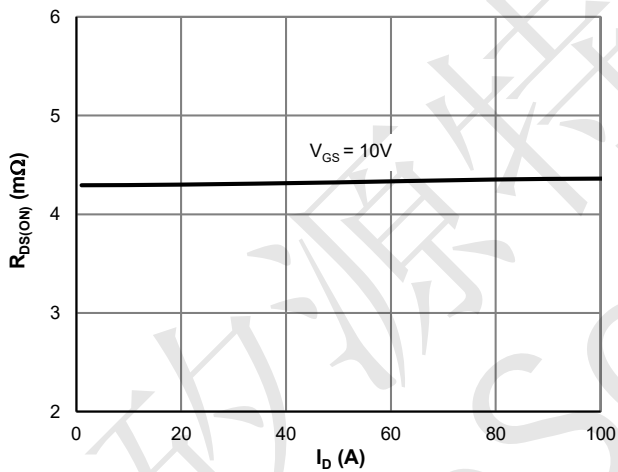


Figure 3: $R_{DS(ON)}$ vs. Drain Current

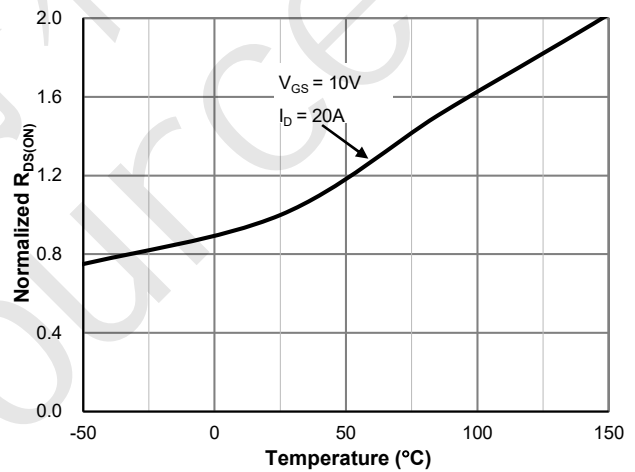


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

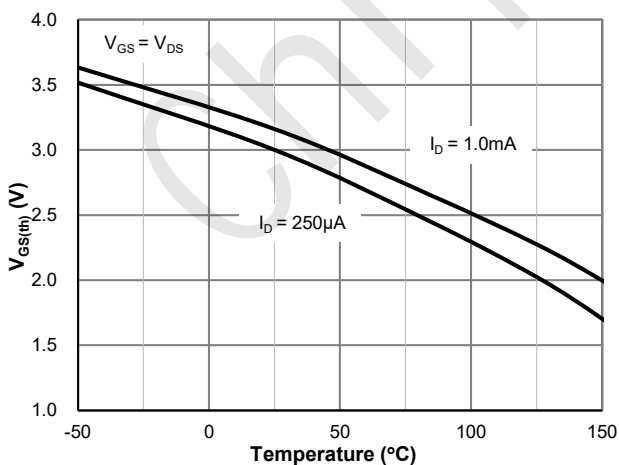


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

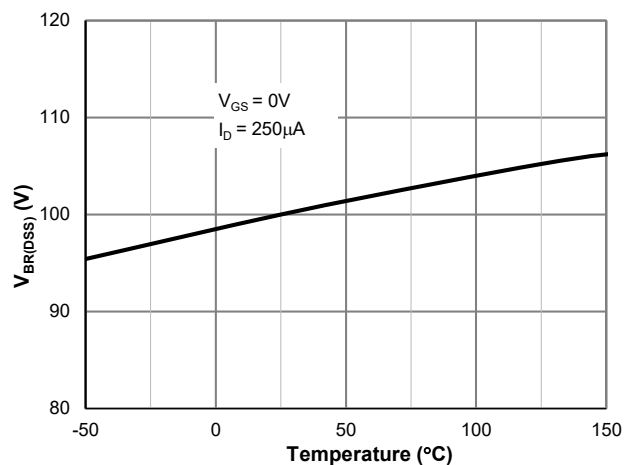


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature



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CSTS150N10G Typical Electrical & Thermal Characteristics

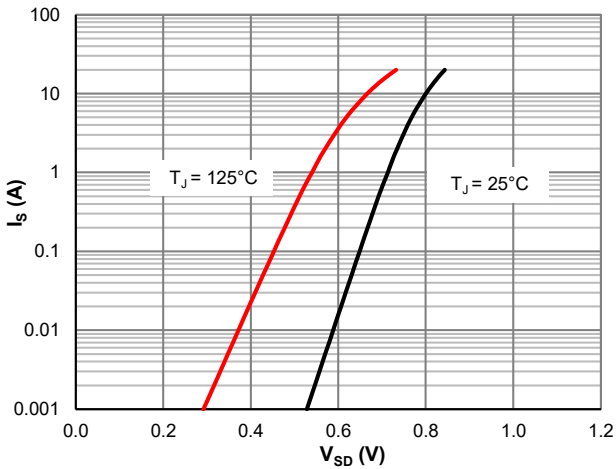


Figure 7: Body-Diode Characteristics

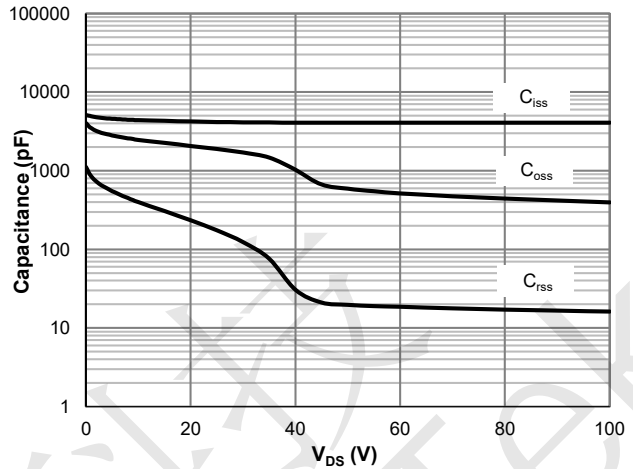


Figure 8: Capacitance Characteristics

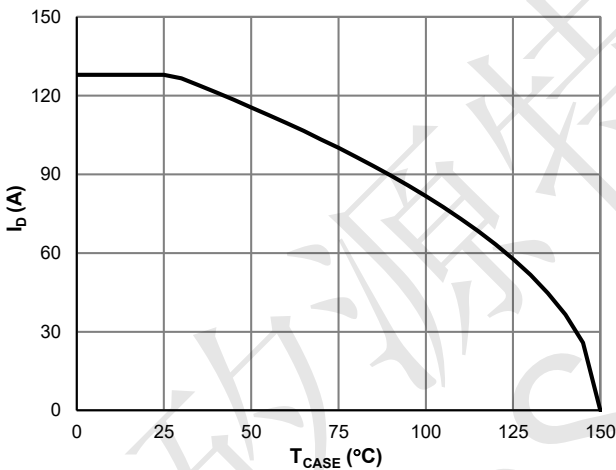


Figure 9: Current De-rating

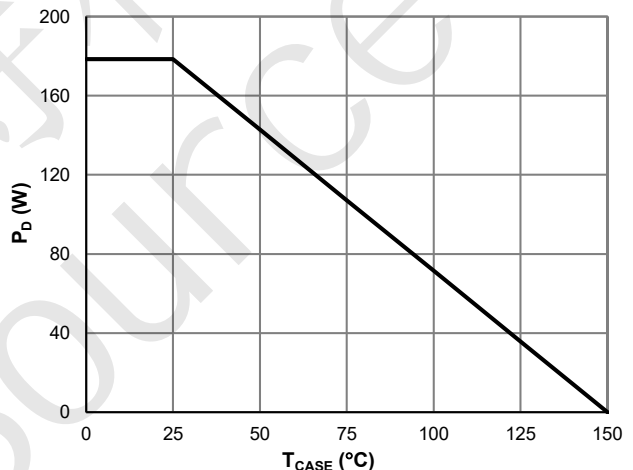


Figure 10: Power De-rating

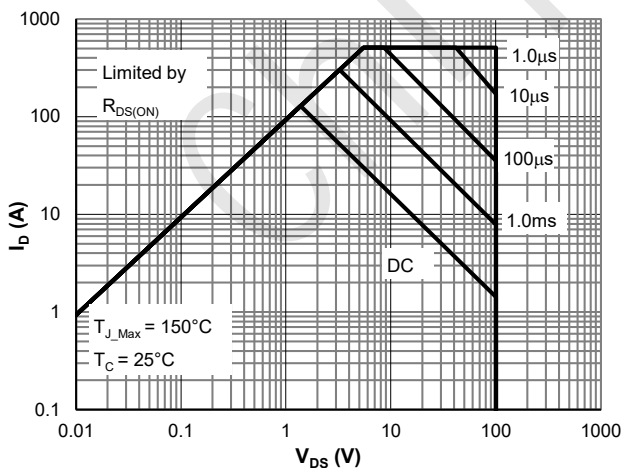


Figure 11: Maximum Safe Operating Area

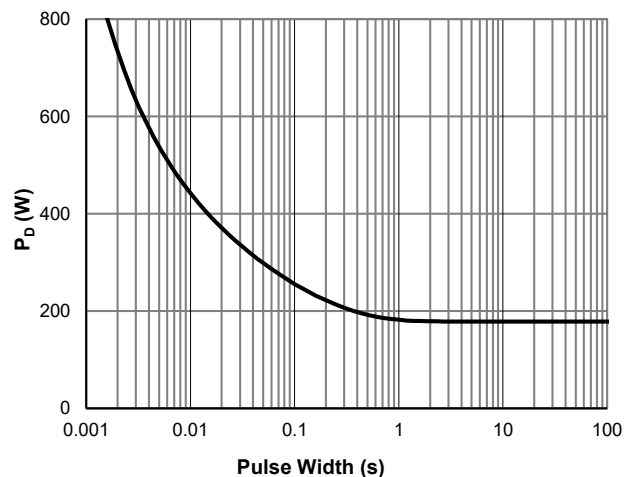


Figure 12: Single Pulse Power Rating, Junction-to-Case



CSTS150N10G Typical Electrical & Thermal Characteristics

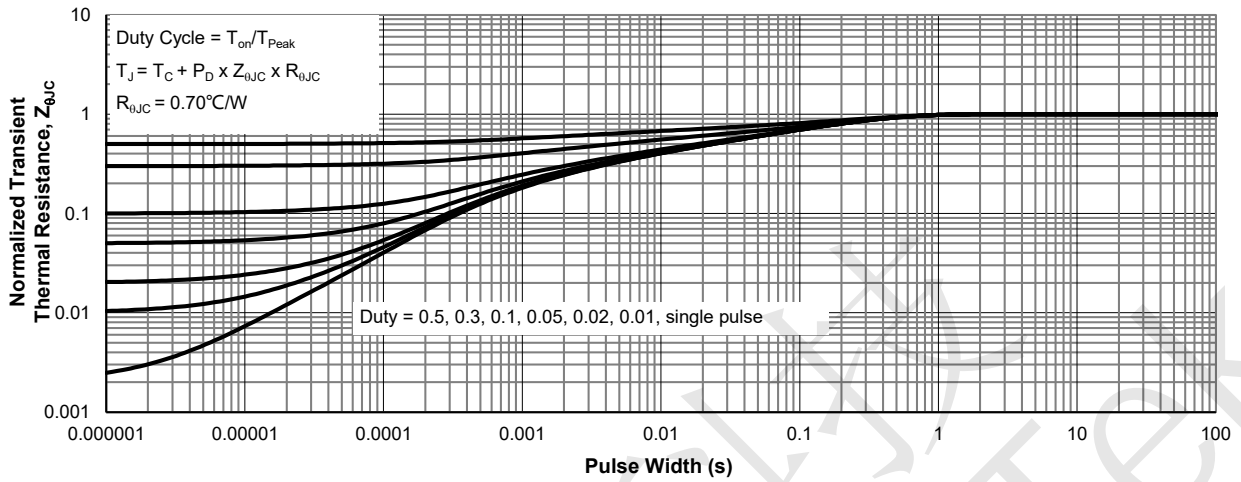
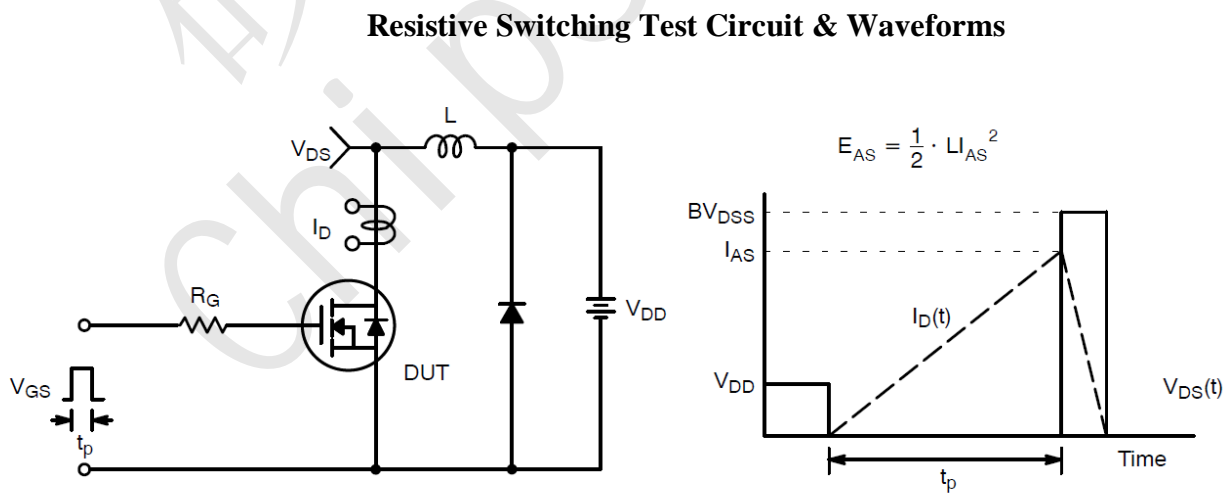
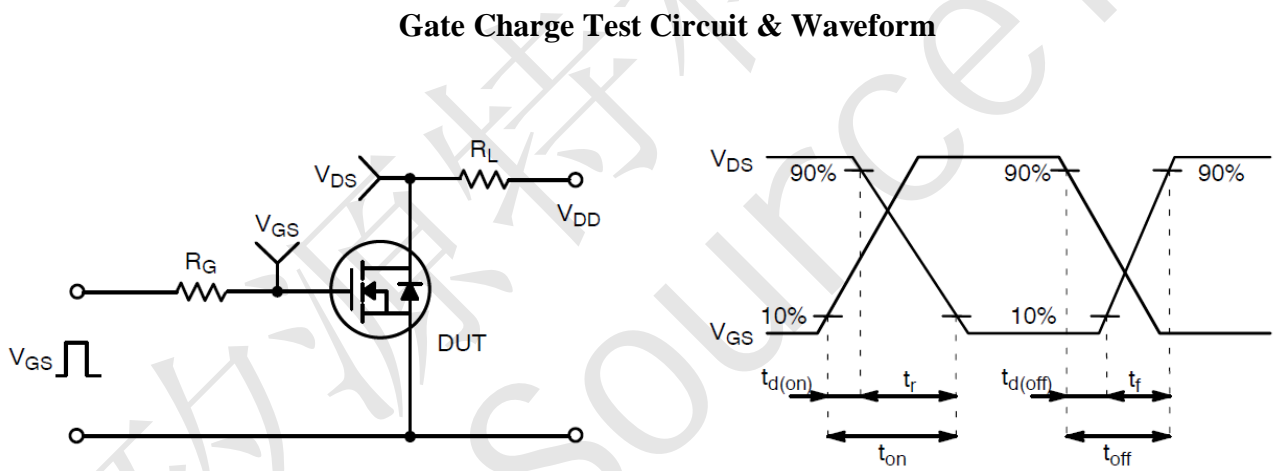
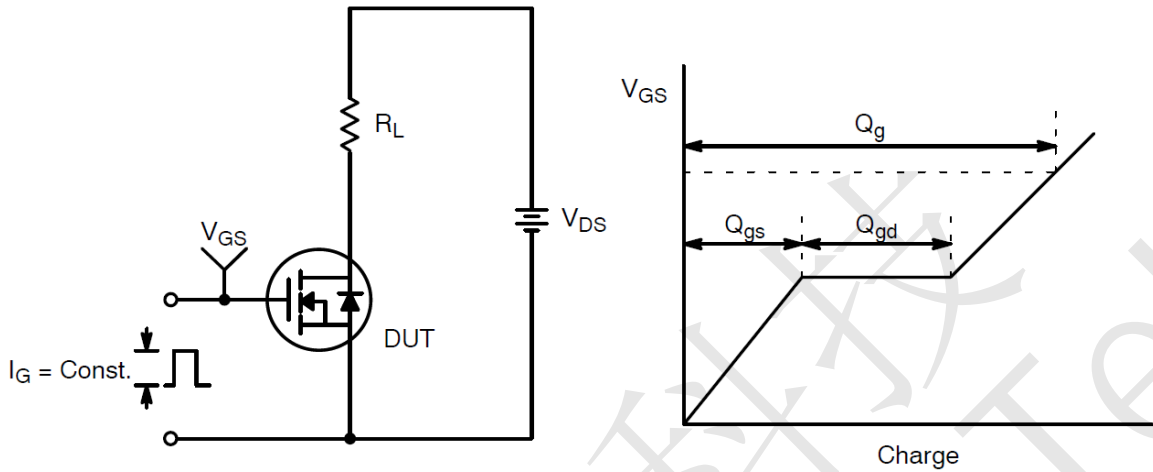


Figure 13: Normalized Maximum Transient Thermal Impedance



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CSTS150N10G Test Circuit and Waveform:

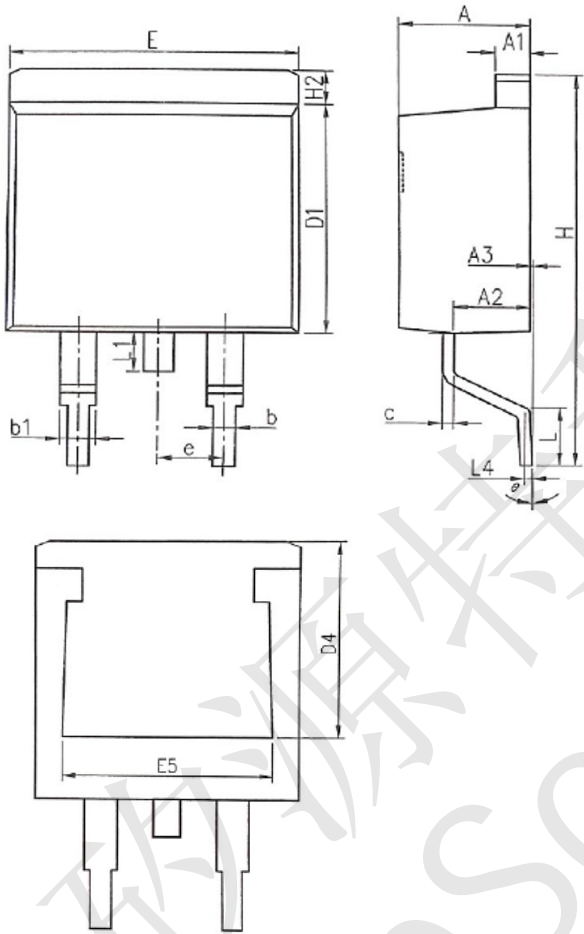




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CSTS150N10G Mechanical Dimensions for TO-263

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°